

multilayer structure including an amorphous layer and a crystalline layer formed on the amorphous layer, both the amorphous layer and the crystalline layer being made of boron phosphide (BP), and the gallium nitride phosphide single crystal layer being made of $\text{GaN}_{0.97}\text{P}_{0.03}$ is formed in contact with the crystalline layer of boron phosphide.

B²
16. (Amended) A method for producing a group-III nitride semiconductor light-emitting device, comprising
forming a boron phosphide (BP)-based buffer layer on a single crystal substrate, and
providing a light-emitting part structure containing a gallium nitride phosphide ($\text{GaN}_{1-x}\text{P}_x$, wherein $0 < x < 1$) single crystal layer provided via a boron phosphide (BP)-based buffer layer, wherein the boron phosphide-based buffer layer comprises a multilayer structure including an amorphous layer and a crystalline layer formed on the amorphous layer, both the amorphous layer and the crystalline layer being made of boron phosphide (BP), and the gallium nitride phosphide single crystal layer being made of $\text{GaN}_{0.97}\text{P}_{0.03}$ is formed in contact with the crystalline layer of boron phosphide.
